

THYRISTOR(Through Hole/Isolated)

SMG12C60F

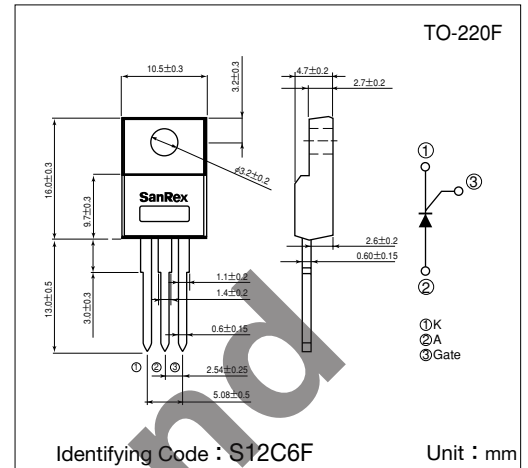
SanRex Thyristor SMG12C60F is designed for full wave AC control applications. It can be used as an ON/OFF function or for phase control operation.

Typical Applications

- Home Appliances : Electric Blankets, Starter for FL, other control applications
- Industrial Use : SMPS, Solenoid for Breakers, Motor Controls, Heater Controls, other control applications

Features

- $I_{T(AV)}=12A$
- High Surge Current
- Low Voltage Drop
- Lead-Free Package



Maximum Ratings

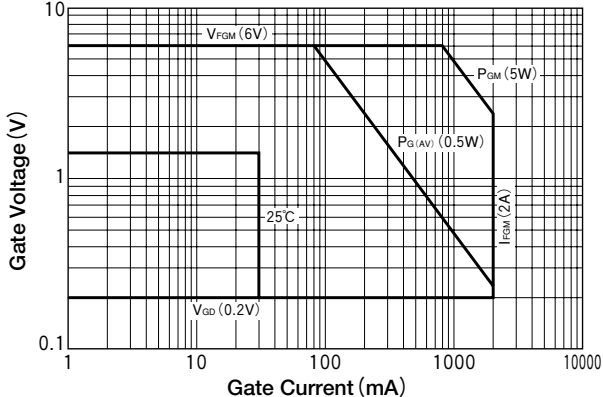
($T_j=25^\circ\text{C}$ unless otherwise specified)

| Symbol | Item | Reference | Ratings | Unit |
|--------------|-------------------------------------|---|-----------------|------------------|
| V_{RRM} | Repetitive Peak Reverse Voltage | | 600 | V |
| V_{RSM} | Non-Repetitive Peak Reverse Voltage | | 720 | V |
| V_{DRM} | Repetitive Peak Off-State Voltage | | 600 | V |
| $I_{T(AV)}$ | Average On-State Current | Single phase, half wave, 180° conduction, $T_c=68^\circ\text{C}$ | 12 | A |
| $I_{T(RMS)}$ | R.M.S. On-State Current | Single phase, half wave, 180° conduction, $T_c=68^\circ\text{C}$ | 18.8 | A |
| I_{TSM} | Surge On-State Current | 50Hz/60Hz, $\frac{1}{2}$ cycle Peak value, non-repetitive | 180/197 | A |
| I^2t | I^2t | | 162 | A^2S |
| P_{GM} | Peak Gate Power Dissipation | | 5 | W |
| $P_{G(AV)}$ | Average Gate Power Dissipation | | 0.5 | W |
| I_{FGM} | Peak Gate Current | | 2 | A |
| V_{FGM} | Peak Gate Voltage (Forward) | | 6 | V |
| V_{RGM} | Peak Gate Voltage (Reverse) | | 10 | V |
| V_{ISO} | Isolation Breakdown (R.M.S.) | A.C 1minute | 1500 | V |
| T_j | Operating Junction Temperature | | $-40 \sim +125$ | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature | | $-40 \sim +150$ | $^\circ\text{C}$ |
| | Mass | | 2 | g |

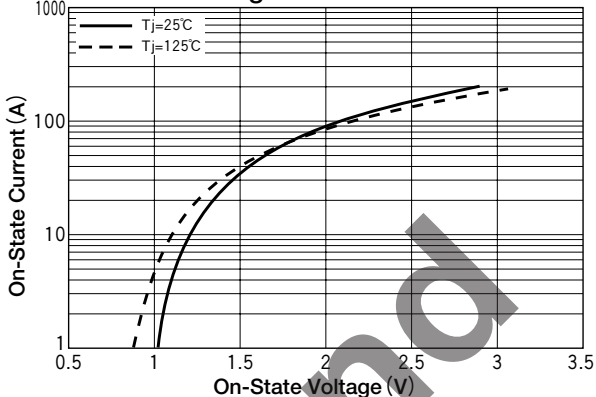
Electrical Characteristics

| Symbol | Item | Reference | Ratings | | | Unit |
|---------------|-----------------------------------|--|---------|------|------|--------------------|
| | | | Min. | Typ. | Max. | |
| I_{DRM} | Repetitive Peak Off-State Current | $T_j=125^\circ\text{C}$, $V_D=V_{DRM}$, | | | 2 | mA |
| I_{RRM} | Repetitive Peak Reverse Current | $T_j=125^\circ\text{C}$, $V_R=V_{RRM}$, | | | 2 | mA |
| V_{TM} | Peak On-State Voltage | $I_T=35A$, Inst. measurement | | | 1.5 | V |
| I_{GT} | Gate Trigger Current | $V_D=6V$, $R_L=10\Omega$ | | | 30 | mA |
| V_{GT} | Gate Trigger Voltage | | | | 1.4 | V |
| V_{GD} | Non-Trigger Gate Voltage | $T_j=125^\circ\text{C}$, $V_D=\frac{1}{2}V_{DRM}$, | 0.2 | | | V |
| I_H | Holding Current | | | 15 | | mA |
| $R_{th(j-c)}$ | Thermal Resistance | Junction to case | | | 3.3 | $^\circ\text{C/W}$ |

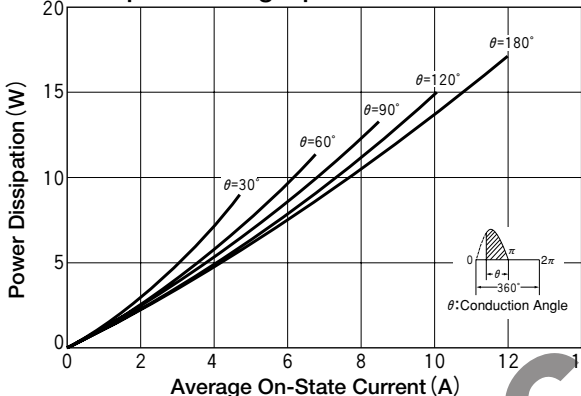
Gate Characteristics



On-State Voltage Max



Average On-State Current vs Power Dissipation (Single phase half wave)



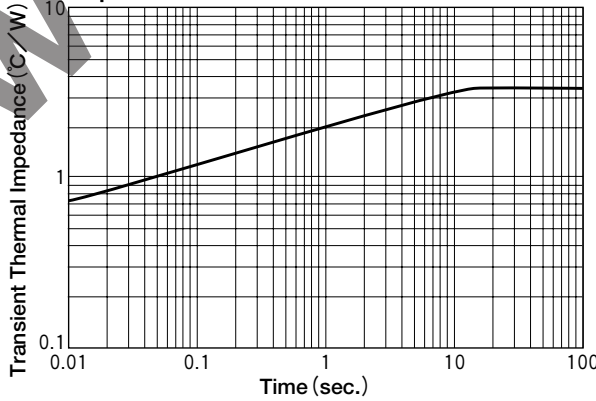
Average On-State Current vs Ambient Temperature (Single phase half wave)



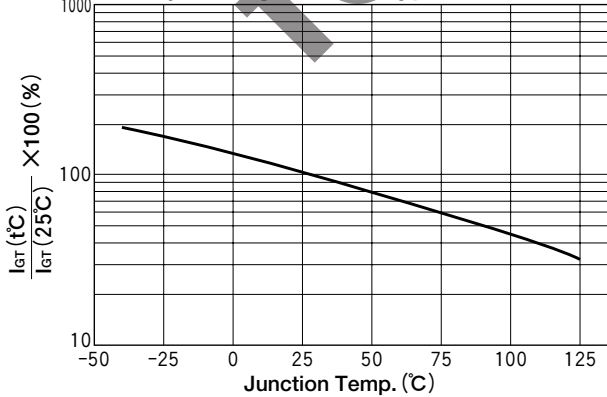
Surge On-State Current Rating (Non-Repetitive)



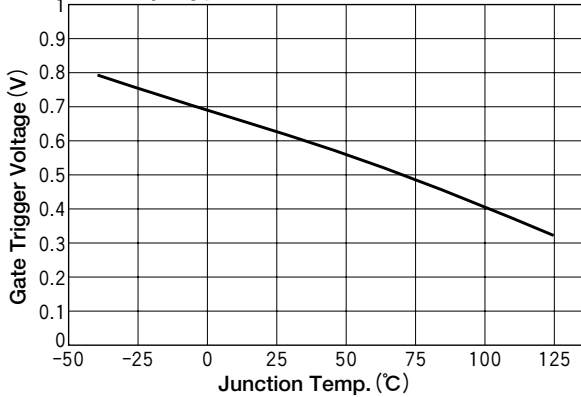
Maximum Transient Thermal Impedance Characteristics

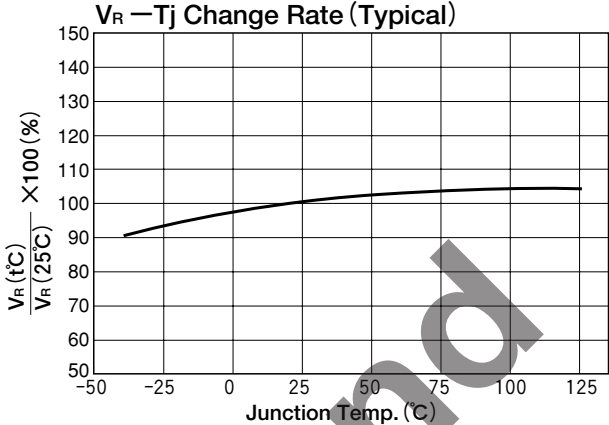
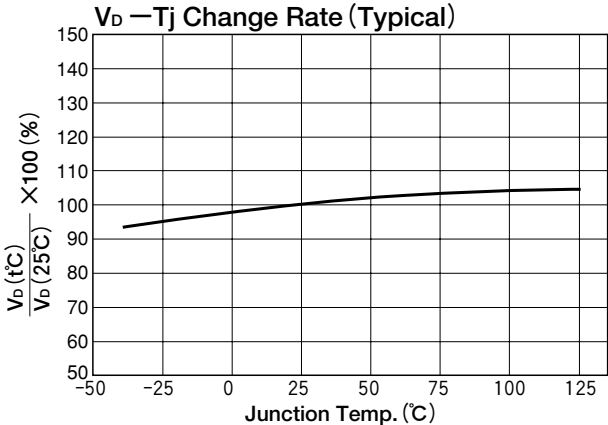


I_{GT} - T_j [Change Rate] (Typical)



V_{GT} - T_j (Typical)





Not Recommended for New Design